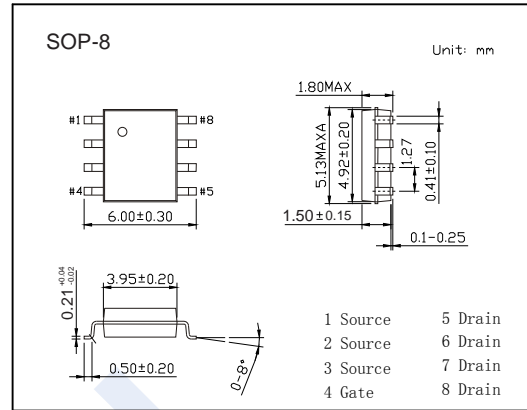
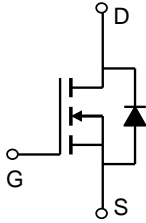


N-Channel MOSFET

AO4430 (KO4430)

■ Features

- $V_{DS} (V) = 30V$
- $I_D = 18 A (V_{GS} = 10V)$
- $R_{DS(ON)} < 5.5m\Omega (V_{GS} = 10V)$
- $R_{DS(ON)} < 7.5m\Omega (V_{GS} = 4.5V)$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	V_{DS}	30	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current	I_D	$T_A=25^\circ C$	18	A
		$T_A=70^\circ C$	15	
Pulsed Drain Current	I_{DM}	80		
Avalanche Current	I_{AR}	30		
Repetitive Avalanche Energy	$L=0.3mH$	E_{AR}	135	mJ
Power Dissipation	P_D	$T_A=25^\circ C$	3	W
		$T_A=70^\circ C$	2.1	
Thermal Resistance.Junction- to-Ambient	R_{thJA}	$t \leq 10s$	40	$^\circ C/W$
		Steady-State	75	
Thermal Resistance.Junction- to-Lead	R_{thJL}	24		
Junction Temperature	T_J	150	$^\circ C$	
Storage Temperature Range	T_{stg}	-55 to 150		

N-Channel MOSFET

AO4430 (KO4430)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =250 μA, V _{GS} =0V	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V			1	μA
		V _{DS} =30V, V _{GS} =0V, T _J =55°C			5	
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250 μA	1		2.5	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =18A			5.5	mΩ
		V _{GS} =20V, I _D =18A, T _J =125°C			8	
		V _{GS} =4.5V, I _D =15A			7.5	
On State Drain Current	I _{D(ON)}	V _{GS} =4.5V, V _{DS} =5V	80			A
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =18A		82		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =15V, f=1MHz	4660		7270	pF
Output Capacitance	C _{oss}		425		960	
Reverse Transfer Capacitance	C _{rss}		240		530	
Gate Resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz	0.2		0.9	Ω
Total Gate Charge (10V)	Q _g	V _{GS} =10V, V _{DS} =15V, I _D =18A	80		124	nC
Total Gate Charge (4.5V)			37		58	
Gate Source Charge	Q _{gs}			18		
Gate Drain Charge	Q _{gd}			15		
Turn-On DelayTime	t _{d(on)}		V _{GS} =10V, V _{DS} =15V, R _L =0.83Ω, R _{GEN} =3Ω		12	
Turn-On Rise Time	t _r			8	12	
Turn-Off DelayTime	t _{d(off)}			51.5	70	
Turn-Off Fall Time	t _f			8.8	14	
Body Diode Reverse Recovery Time	t _{rr}	I _F =18A, di/dt=100A/μs		33.5	44	nA
Body Diode Reverse Recovery Charge	Q _{rr}			22	30	
Maximum Body-Diode Continuous Current	I _S				4.5	A
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V			1	V

Note : The static characteristics in Figures 1 to 6 are obtained using <300 us pulses, duty cycle 0.5% max.

■ Marking

Marking	4430
	KC****

N-Channel MOSFET AO4430 (KO4430)

■ Typical Characteristics

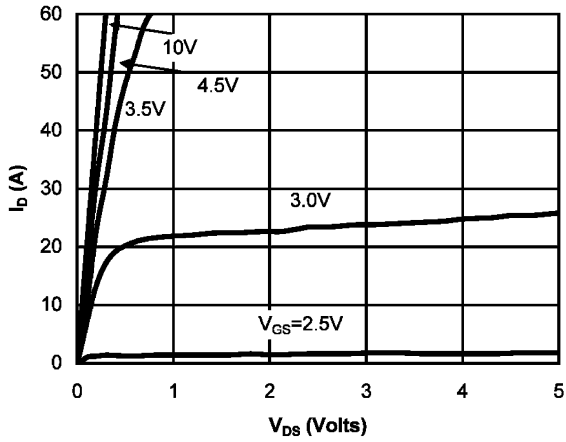


Fig 1: On-Region Characteristics

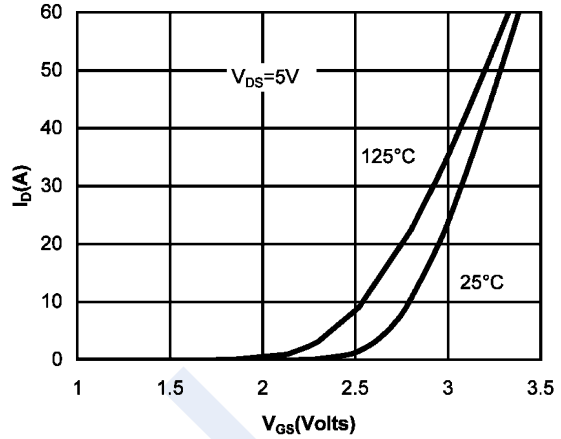


Figure 2: Transfer Characteristics

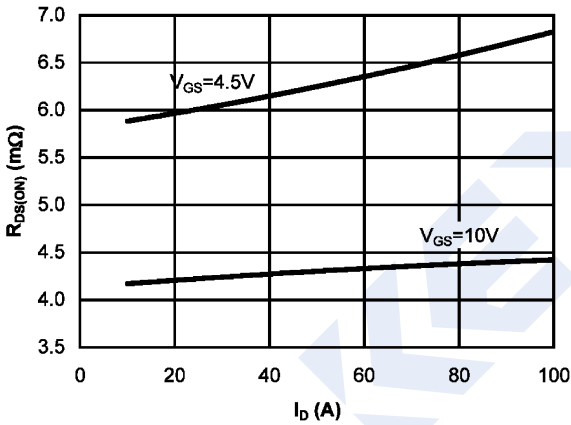


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

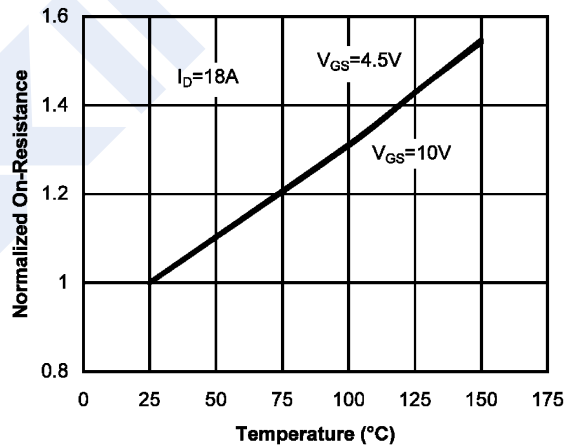


Figure 4: On-Resistance vs. Junction Temperature

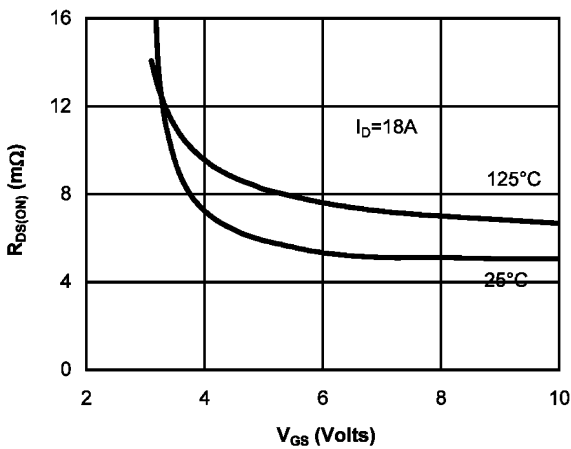


Figure 5: On-Resistance vs. Gate-Source Voltage

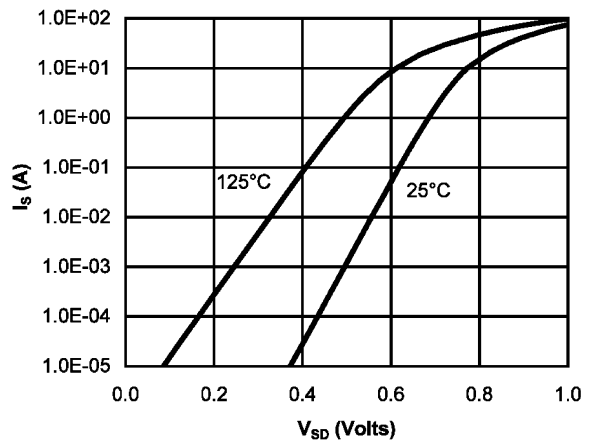


Figure 6: Body-Diode Characteristics

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■ Typical Characteristics

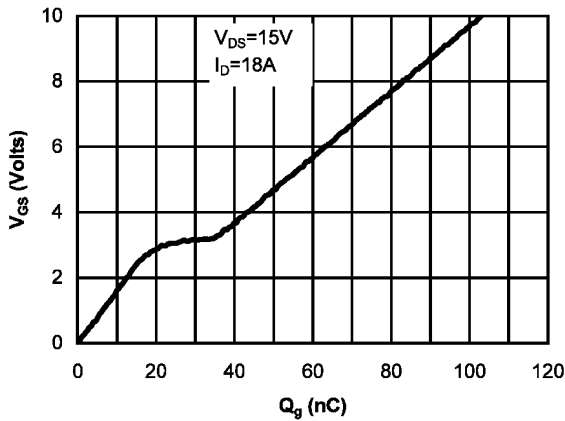


Figure 7: Gate-Charge Characteristics

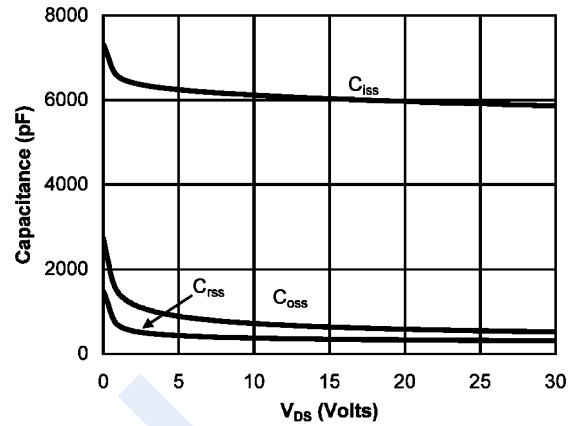


Figure 8: Capacitance Characteristics

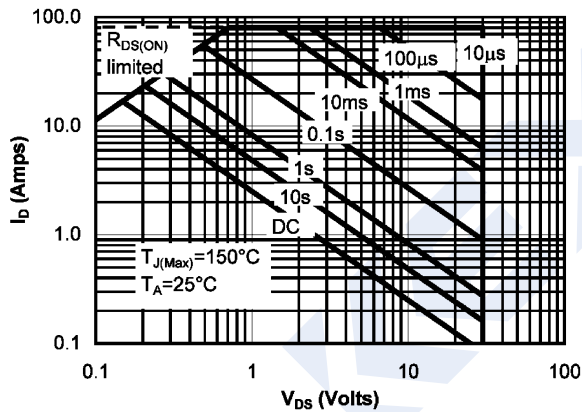


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

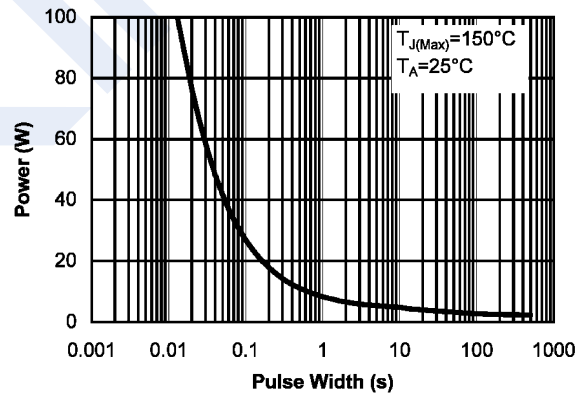


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

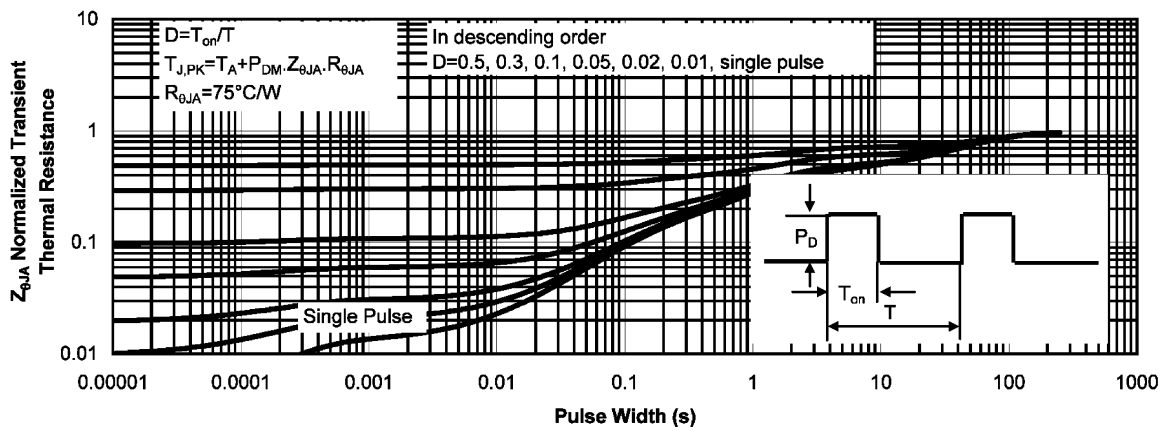


Figure 11: Normalized Maximum Transient Thermal Impedance